

AlGaInP Red LED chip

Type:
708SRAP-R-AU-01

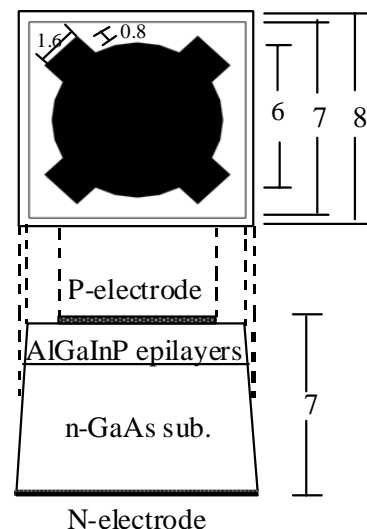
Features:

- (1) High luminous intensity
- (2) Long operation life
- (3) 100% probing test
- (4) Low driving current applications

unit: mil

Characteristics:

- (1) Size
 Chip Size: 8 mil x 8 mil ($203 \pm 25 \mu\text{m} \times 203 \pm 25 \mu\text{m}$)
 Chip Thickness: 7 mil ($180 \pm 25 \mu\text{m}$) typical
 Bonding Pad: 6 mil ($152 \pm 10 \mu\text{m}$) in diameter
- (2) Metallization:
 P electrode : Au pad
 N electrode : Au alloy
- (3) Structure:
 Refer to drawing



Electro-optical characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Forward voltage	V_{f1}	$I_f = 10\mu\text{A}$	1.25	---	---	V	
	V_{f2}	$I_f = 6.3\text{mA}$	---	2.0	2.4	V	
Reverse voltage	V_r	$I_r = 10\mu\text{A}$	9	---	---	V	
Dominant wavelength ⁽¹⁾	λ_p	$I_f = 6.3\text{mA}$	650	---	685	nm	
Luminous intensity ⁽²⁾⁽³⁾	P_o	A	$I_f = 6.3\text{mA}$	0.016	---	0.036	mW

- (1) Basically, wavelength uniformity is $\lambda_d \pm 5\text{nm}$; however, customers' special requirements are also welcome.
- (2) Customer's special requirements are also welcome.
- (3) Luminous intensity is measured by EPISTAR's equipment on bare chips.

Hints: Bonding temperature => Do not apply over 280°C on chip for 10 seconds.